

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

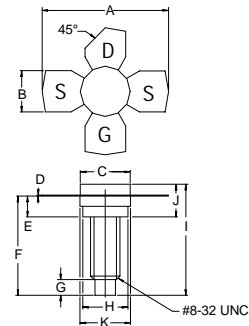
The **ASI BLV30** is Designed for Television Band IV & V Applications up to 860 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 10$  dB at 2.0 W/860 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.5 A
$V_{CBO}$	60 V
$V_{CEO}$	30 V
$V_{EBO}$	4.0 V
$P_{DISS}$	15.9 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	$10^\circ\text{C/W}$

**PACKAGE STYLE .280 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 10$ mA	60			V
$BV_{CEO}$	$I_C = 50$ mA	30			V
$BV_{EBO}$	$I_E = 4.0$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 30$ V			4.0	mA
$h_{FE}$	$V_{CE} = 25$ V $I_C = 500$ mA	15		120	---
$C_{OB}$	$V_{CB} = 28$ V $f = 1.0$ MHz			10	pF
$P_G$	$V_{CE} = 25$ V $I_C = 410$ mA $f = 860$ MHz	10			dB
$IMD_1$	$P_{OUT} = 2.0$ W	-60			dBc

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

[LittleDiode.com](http://LittleDiode.com)

Looking forward to providing you with the best possible service.